	<p>Hersteller-Teilenummer: SI2318CDS-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET N-CH 40V 5.6A SOT-23</p>
	<p>Datenblätter:  SI2318CDS-T1-GE3.pdf</p>
<p>RoHs Status: Bleifrei / RoHS-konform</p>	<p>Lagerzustand: New original, 81503 pcs Stock Available.</p>
<p>Lieferung von: Hong Kong</p>	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2318CDS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 40V 5.6A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	81503 pcs Stock
Hersteller Standard Vorlaufzeit	27 Weeks
detaillierte Beschreibung	N-Channel 40V 5.6A (Tc) 1.25W (Ta), 2.1W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.25W (Ta), 2.1W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.6A (Tc)
Rds On (Max) @ Id, Vgs	42 mOhm @ 4.3A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	9nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	340pF @ 20V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2318CDS-T1-GE3CT

















SI2318CDS-T1-GE3 ist neu im Original. Suche SI2318CDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2318CDS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2318CDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2318BDS-T1-GE3 VISHAY SI2318BDS-T1-GE3 VISHAY</p>	 <p>SI2318CDS-T1-E3 VISHAY SI2318CDS-T1-E3 VISHAY</p>	 <p>SI2318BDS-T1-E3 VISHAY SI2318BDS-T1-E3 VISHAY</p>	 <p>SI2318DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 3A SOT23-3</p>
 <p>SI2318CDS Vishay Precision Group SI2318CDS VISHAY</p>	 <p>SI2318DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 3A SOT-23</p>	 <p>SI2318CDS-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 5.6A SOT-23</p>	 <p>SI2318DS VISHAY/ SI2318DS VISHAY/</p>

heiße Teile

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|--|--|--|--|--|
|  SI2315BDS |  SI2315BDS-T1-E3 |  SI2315BDS-T1-E3 |  SI2315BDS-T1-GE3 |  SI2315BDS-T1-GE3 |
|  SI2315DS |  SI2315DS-T1 |  SI2315DS-T1-E3 |  SI2315DS-T1-GE3 |  SI2316-DS |
|  SI2316BDS-T1-E3 |  SI2316BDS-T1-E3 |  SI2316BDS-T1-GE3 |  SI2316BDS-T1-GE3 |  SI2316DS |
|  SI2316DS-T1-E3 |  SI2316DS-T1-E3 |  SI2316DS-T1-GE3 |  SI2316DS-T1-GE3 |  SI2317DS |
|  SI2317DS-T1-E3 |  SI2318ADS-T1-GE3 |  SI2318BDS-T1-E3 |  SI2318BDS-T1-GE3 |  SI2318CDS-T1-E3 |
|  SI2318CDS-T1-GE3 |  SI2318DS |  SI2318DS-T1-E3 |  SI2318DS-T1-E3 |  SI2318DS-T1-GE3 |
|  SI2318DS-T1-GE3 |  SI2319ADS-T1-GE3 |  SI2319C95TF |  SI2319CDS-T1-E3 |  SI2319CDS-T1-GE3 |
|  SI2319CDS-T1-GE3 |  SI2319DDS-T1-GE3 |  SI2319DS |  SI2319DS-T1-E3 |  SI2319DS-T1-E3 |
|  SI2319DS-T1-GE3 |  SI2319DS-T1-GE3 |  SI2320DS |  SI2320DS-T1-E3 |  SI2320DS-T1-GE3 |
|  SI2321DS-T1-E3 |  SI2321DS-T1-E3 |  SI2321DS-T1-GE3 |  SI2321DS-T1-GE3 |  SI2323CDS-T1 |

Contact us:Info@Y-IC.com

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